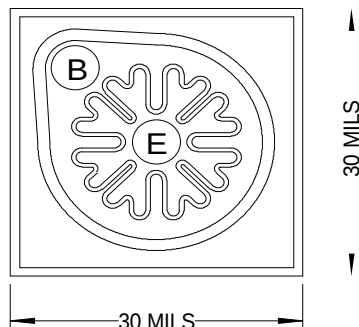


**Chip Type 2C3762**  
**Geometry 6706**  
**Polarity PNP**

### Generic Packaged Parts:

**2N3467, 2N3467L, 2N3468,  
2N3468L, 2N3762, 2N3762L,  
2N3763, 2N3763L, 2N3764, 2N3765**


[Request Quotation](#)

Chip type **2C3762** by Semicoa Semiconductors provides performance similar to these devices.

### Part Numbers:

[2N3467, 2N3467L, 2N3468, 2N3468L,  
2N3762, 2N3762L, 2N3763, 2N3763L,  
2N3764, 2N3765](#)

### Product Summary:

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Features:** [Radiation graphs available](#)

## Mechanical Specifications

|                         |                   |                     |
|-------------------------|-------------------|---------------------|
| <b>Metallization</b>    | Top               | Al - 20 kÅ min.     |
|                         | Backside          | Au - 6.5 kÅ nom.    |
| <b>Bonding Pad Size</b> | Emitter           | 5.0 mils x 5.0 mils |
|                         | Base              | 5.0 mils x 5.0 mils |
| <b>Die Thickness</b>    | 8 mils nominal    |                     |
| <b>Chip Area</b>        | 30 mils x 30 mils |                     |
| <b>Top Surface</b>      | Silox Passivated  |                     |

## Electrical Characteristics

 $T_A = 25^{\circ}\text{C}$ 

| Parameter  | Test conditions                                  | Min | Max | Unit |
|------------|--------------------------------------------------|-----|-----|------|
| $BV_{CBO}$ | $I_C = 100 \mu\text{A}, I_E = 0$                 | 140 | --- | V dc |
| $BV_{EBO}$ | $I_E = 100 \mu\text{A}, I_C = 0$                 | 7.0 | --- | V dc |
| $I_{CBO}$  | $V_{CB} = 40 \text{ V}, I_E = 0$                 | --- | 10  | nA   |
| $h_{FE}$   | $I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V}$ | 100 | 300 | ---  |

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*